Plastic Infrared Emitting Diode

OP265WPS



Features:

- T-1 (3 mm) package style
- Broad irradiance pattern
- · Point source with flat lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm diode



Description:

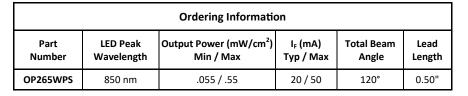
The **OP265WPS** point source model is a flat-lensed 850 nm diode with a broad radiation pattern that provides relatively even illumination over a large area. Its stable forward voltage (V_F) vs. temperature characteristic makes this device appropriate for applications where voltage is limited (such as battery operation), while the low rise time/fall time (t/t_f) makes it ideal for high-speed operation.

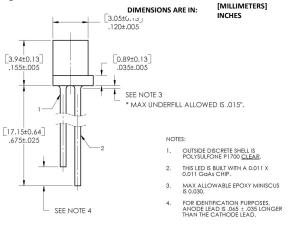
OP265 devices conform to the OP505 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

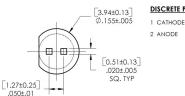
- Space-limited applications
- · Applications requiring coupling efficiency
- Precision optical designs
- Battery-operated or voltage-limited applications







Pin#	LED	
1	Cathode	
2	Anode	





2 ANODE

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' Vibra-Tite for thread-locking. Vibra-Tite evaporates fast without causing structural failure in OPTEK'S molded plastics.



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Electrical Specifications

Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)				
Storage and Operating Temperature Range	-40° C to +100° C			
Reverse Voltage	2.0 V			
Continuous Forward Current	50 mA			
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾			
Power Dissipation	100 mW ⁽²⁾			

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly at 1.33 mW/° C above 25° C.
- 3. E_{E(APT)} is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. E_{E(APT)} is not necessarily uniform within the measured area.

Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode								
E _{E (APT)}	Apertured Radiant Incidence	2.70	-	-	mW/cm ²	I _F = 20 mA ⁽³⁾		
V _F	Forward Voltage	-	-	1.80	V	I _F = 20 mA		
I _R	Reverse Current	-	-	20	μΑ	V _R = 2 V		
λ_{P}	Wavelength at Peak Emission	-	850	-	nm	I _F = 10 mA		
В	Spectral Bandwidth between Half Power Points	-	-	-	nm	I _F = 20 mA		

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Performance OP265WPS

